

.....	5
.....	6
IDM+	6
.....	11
.....	13
100%	14
.....	16
/	19
.....	19
.....	21
.....	24
.....	27
.....	27
.....	29
.....	32
.....	34
.....	35
.....	36

12	2018	12
13		13
14	2018	13
15	2018	14
16		25
17		30
18		31
19		32
20		34
21		35

2018

IDM

IDM

2020

70-90 PE

29.40~37.80

2019~21

58.14/71.72/88.08

-7.3%/23.3%/22.8%

3.74/5.12/8.00

IPO

EPS 0.31/0.42/0.66 /

2020

PE 175x

52x

59x

95x

8

8

MOSFET

2020

IPO

EPS 0.42

/

70~90 PE

29.40~37.80

1

IDM

2

3

IDM+

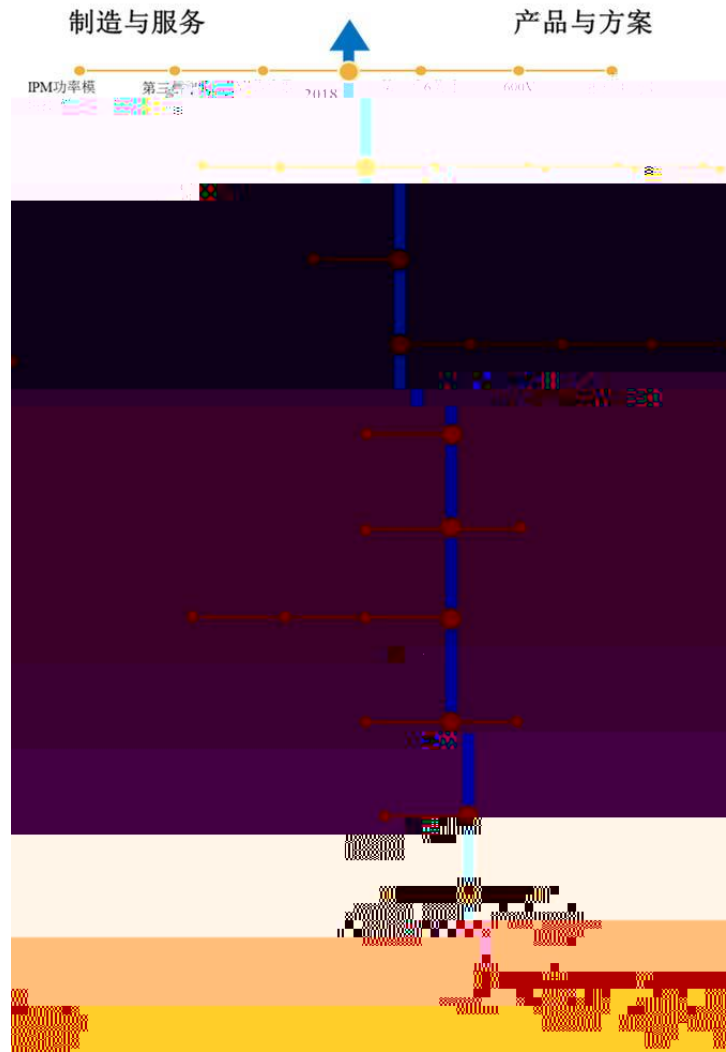
	2019 1-6	2018	2017	2016
	102,793.73	241,885.78	206,857.89	108,118.07
	90.16%	90.14%	88.44%	81.19%
				6.41%

4 IC

AC-DC			
LED IC			
BMSIC			

6

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MPSInternational,Ltd

DiodesIncorporated

10 2018

13

|

TCL
TTi

200.

ID

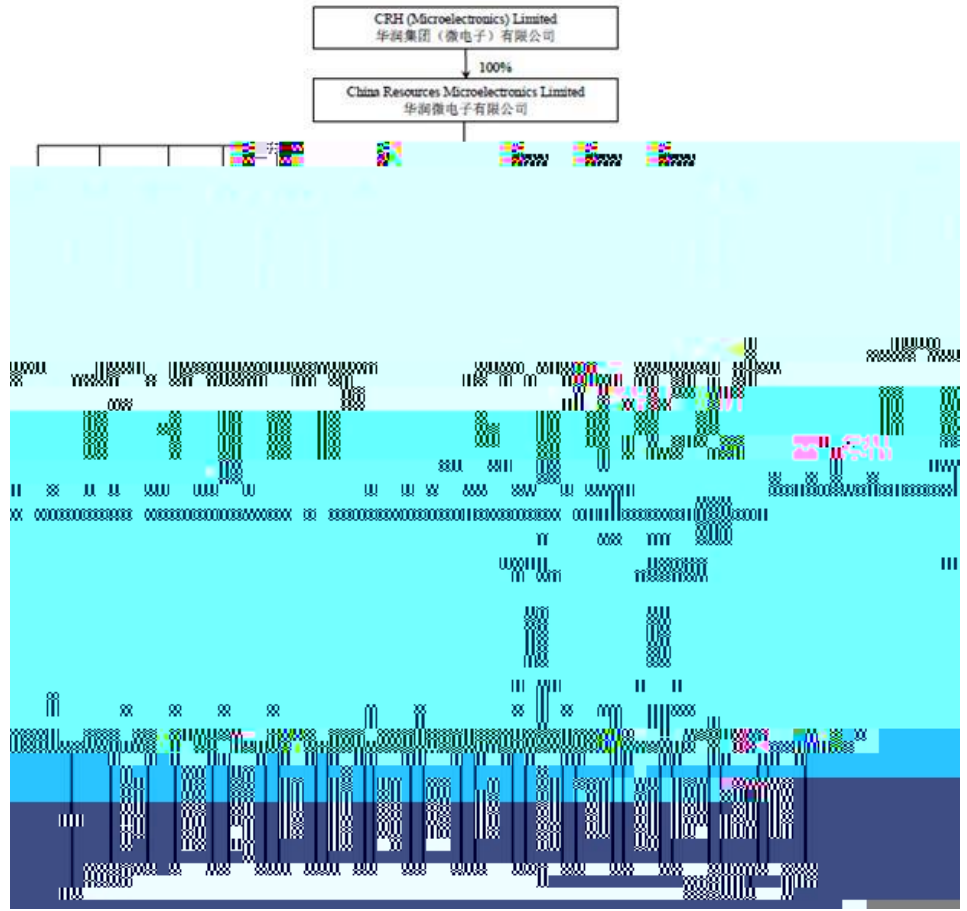
14 2018

--

1

	2018	
--	------	--

2



3



12 2017

13 2018

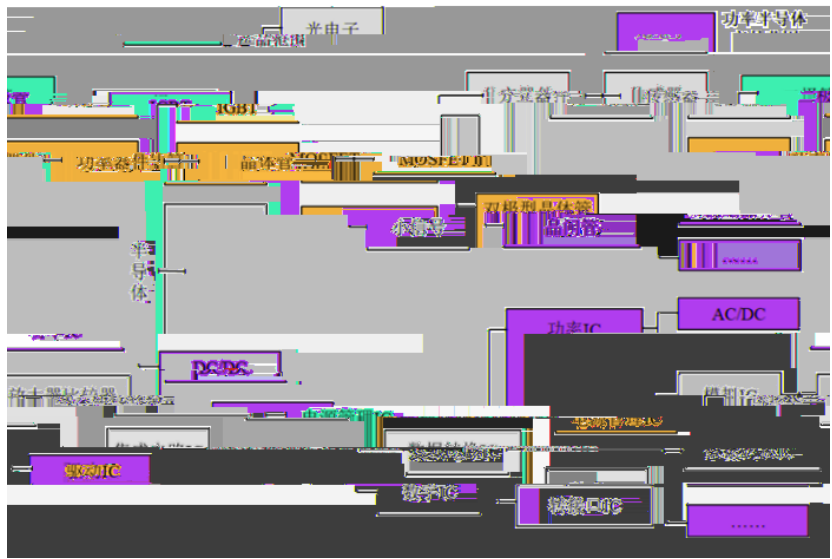
Yole IHS Gartner

IHS Markit

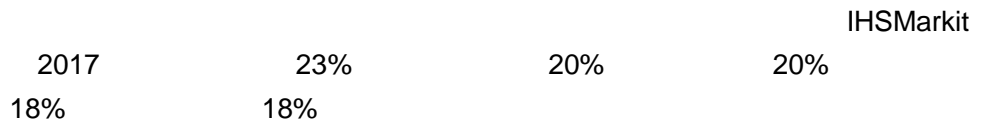
1 IC
IC
IC
IHSMarkit IC
2018
2.88%

GaN SiC

IC 84.3 2016-2018

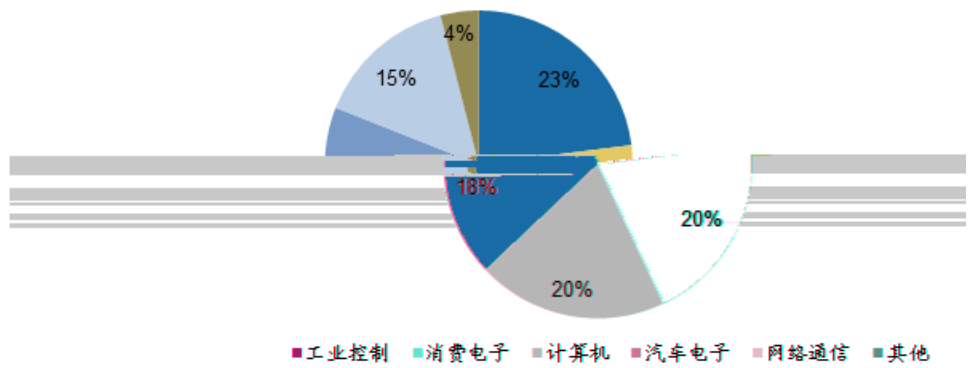


IHS



IHSMarkit

15 2017



IHS Markit

1

MOSFET

IGBT

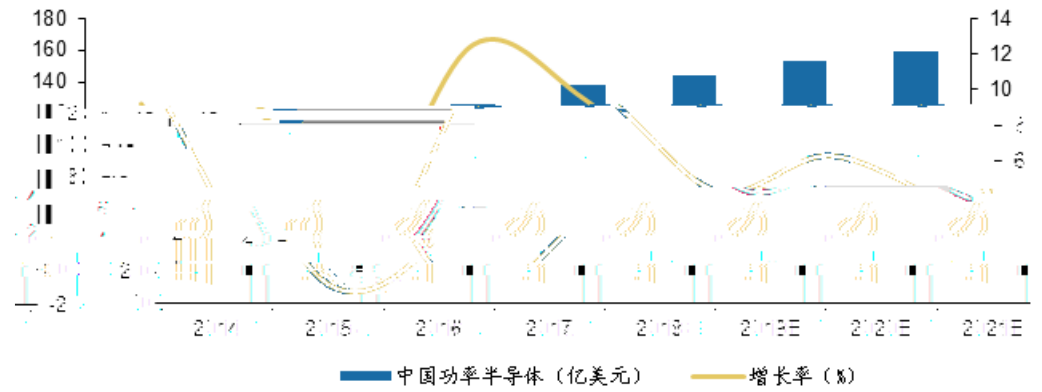
20%	50%	McKinsey&Company			
704		350	2	387	55%
				269	
76%					
	2016	2023		78.86	IHS
136.3			8%		
16					

IHS

2

2025

18 2014-2021



IHS

IGBT
MOSFET
SiC GaN

1.1eV

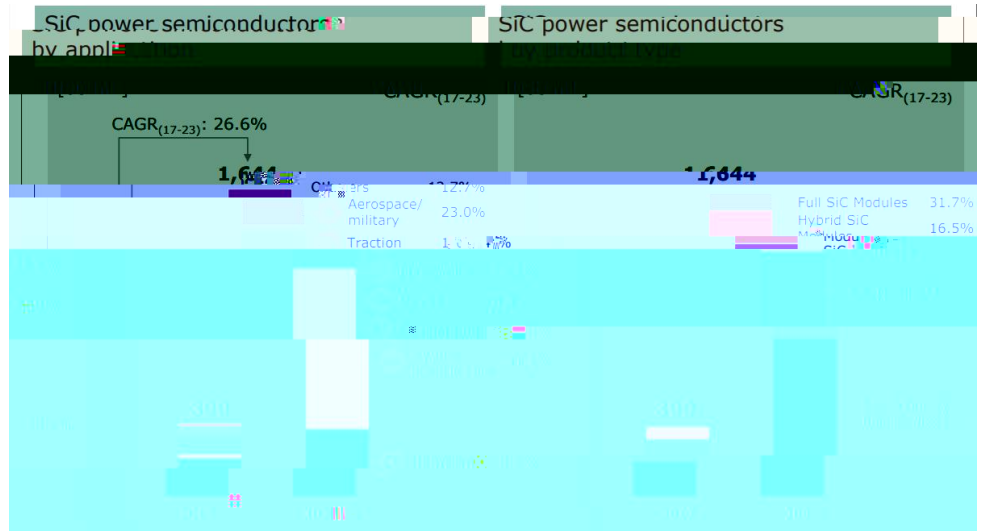
1.4

SiC GaN
5G

16

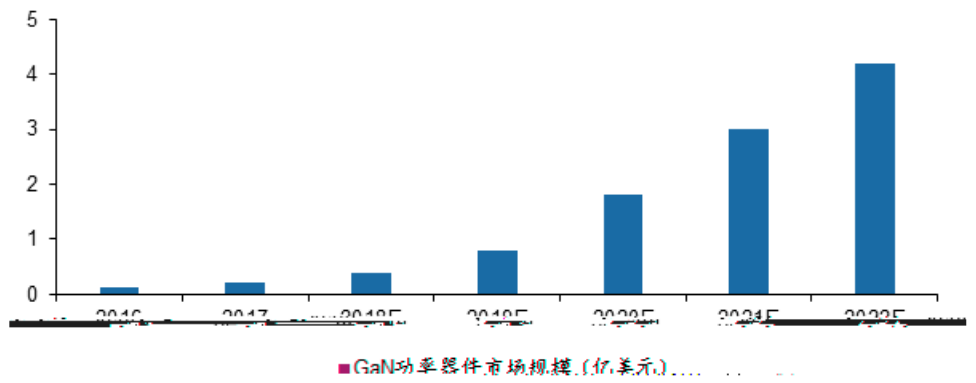
eV	K
1.1	1221
0.7	1678
1.4	1511
3.05	2826

20 SiC

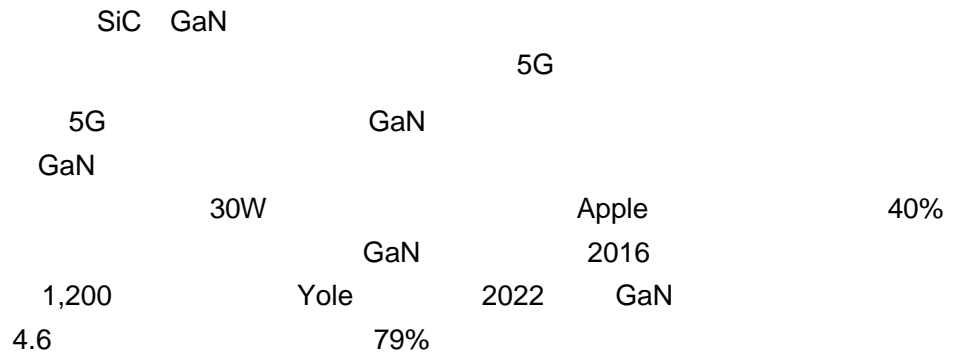


IHS

21 GaN



Yole



MOSFET

iHS

62%

27%

24 2018

MOSFET

IHS

IGBT

IHS

2018

IGBT

67%

34%

600 1700V

650V

400V

2018 IHS 138 2018
391 35% Dialog
42% 14%
26 2018

17

	MOS	1			FOM	MOS	,	MOSFET
			2					
				3				
MOSFET	VDMOS	1			FOM	2		VDMOS
				UIS	3	EMI		
	MOS	1		2				MOS
				FOM	3			
IGBT	IGBT	1	Trench-FS			2		IGBT
				3				

`~%>0ä\$! ùÀ<> s\$; °ñ`ë>

4

2019-2021

60,000.00

72,555.35

2020 5G

IDM

2019/20/21

28.47/30.24/32.13

-20.3%/6.2%/6.3%

14.6%/16.6%/18.6%

2019

IDM

2016 2018

IHS Markit 2018

12 31

2017A 2018A 2019E 2020E 2021E
4,598 5,106 5,191 10,140 11,579

12 31

2017A 2018A 2019E 2020E 2021E

2019

2014

2015

2016

2015

2012

2018

1

2
